General Description

The WSF20N06 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF20N06 meet the RoHS and Green Product requirement .

Product Summery

BVDSS	RDSON	ID
60V	35mΩ	25A

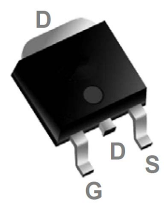
Applications

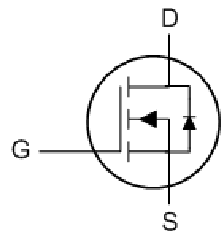
- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- LCD/LED back light

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

TO-252 Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	25	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	27	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	8	A
I_D@T_A=70℃	Continuous Drain Current, V_{GS} @ 10V[1]	10	A
I_{DM}	Pulsed Drain Current[2]	100	A
EAS	Single Pulse Avalanche Energy[3]	38	mJ
I_{AS}	Avalanche Current	14	A
P_D@T_C=25℃	Total Power Dissipation[4]	35	W
P_D@T_A=25℃	Total Power Dissipation[4]	3.3	W
T_{STG}	Storage Temperature Range	-55 to 175	℃
T_J	Operating Junction Temperature Range	-55 to 175	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{θJA}$	Thermal Resistance Junction-Ambient [1]	---	75	℃/W
$R_{θJC}$	Thermal Resistance Junction-Case[1]	---	3	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	0.057	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=16A	---	35	45	mΩ
		V_{GS}=5V , I_D=8A	---	40	50	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, I_D =250uA	1.0	1.6	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.68	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=60V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=60V , V_{GS}=0V , T_J=125℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±16V , V_{DS}=0V	---	---	±10	nA
gfs	Forward Transconductance	V_{DS}=25V , I_D=18A	---	25	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.7	3.4	Ω
Q_g	Total Gate Charge (4.5V)	V_{DS}=30V , V_{GS}=10V , I_D=18A	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	7	---	
Q_{gd}	Gate-Drain Charge		---	5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=30V , V_{GS}=10V , R_G=6.8Ω, I_D=1A	---	18	---	ns
T_r	Rise Time		---	15	---	
$T_{d(off)}$	Turn-Off Delay Time		---	60	---	
T_f	Fall Time		---	31	---	
C_{iss}	Input Capacitance	V_{DS}=30V , V_{GS}=0V , f=1MHz	---	650	---	pF
C_{oss}	Output Capacitance		---	95	---	
C_{rss}	Reverse Transfer Capacitance		---	60	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy[5]	V_{DD}=25V , L=0.1mH , I_{AS}=15A	19	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,6]	$V_G=V_D$=0V , Force Current	---	---	25	A
I_{SM}	Pulsed Source Current[2,6]		---	---	75	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=20A , T_J=25℃	---	---	1.3	V
t_{rr}	Reverse Recovery Time	IF=20A ,dI/dt=100A/μs,TJ=25℃	---	65	---	nS
Q_{rr}	Reverse Recovery Charge		---	85	---	nC

Note :
1.The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper,t<10sec.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=15A
4.The power dissipation is limited by 150℃ junction temperature
5.The Min. value is 100% EAS tested guarantee.
6.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

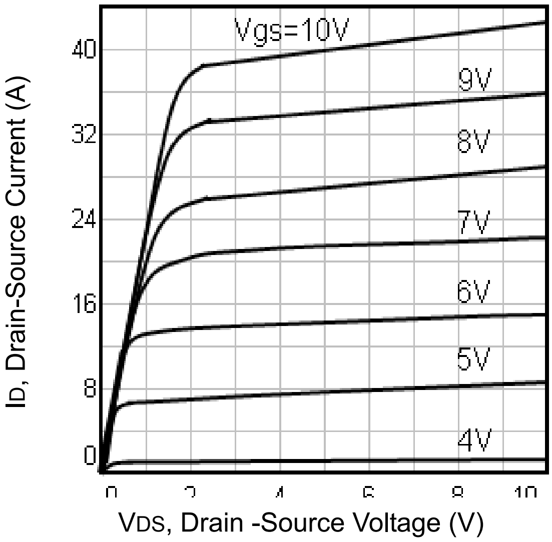
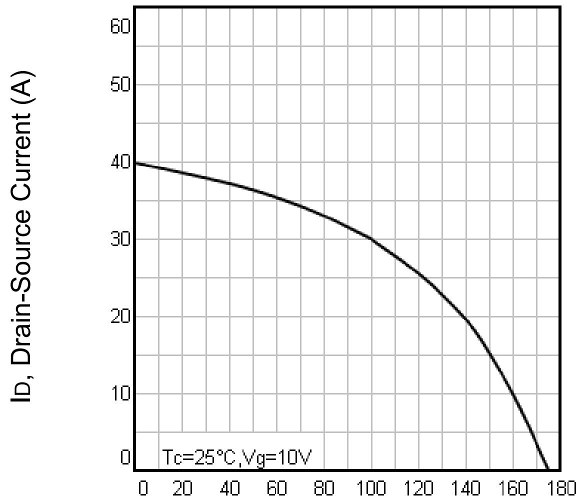


Fig1. Typical Output Characteristics



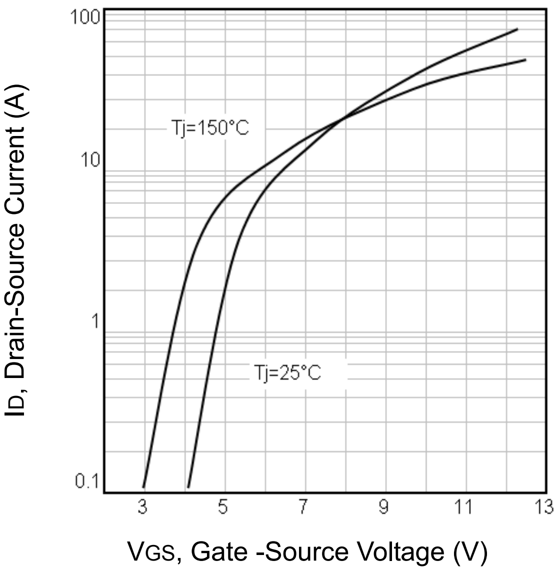


Fig3. Typical Transfer Characteristics

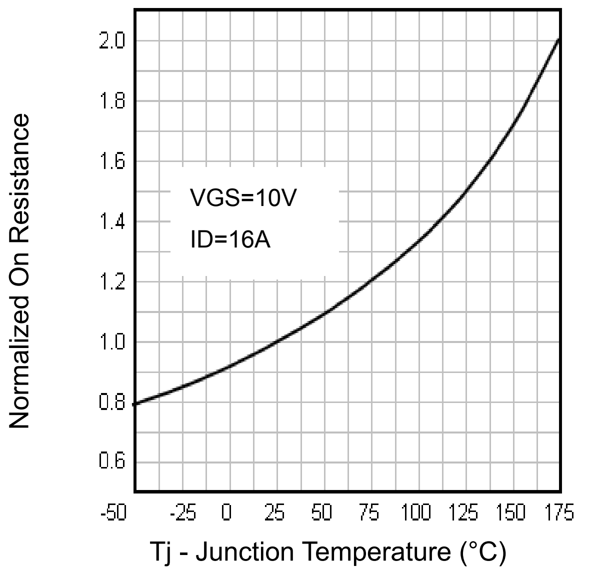


Fig4. Normalized On-Resistance Vs. Temperature

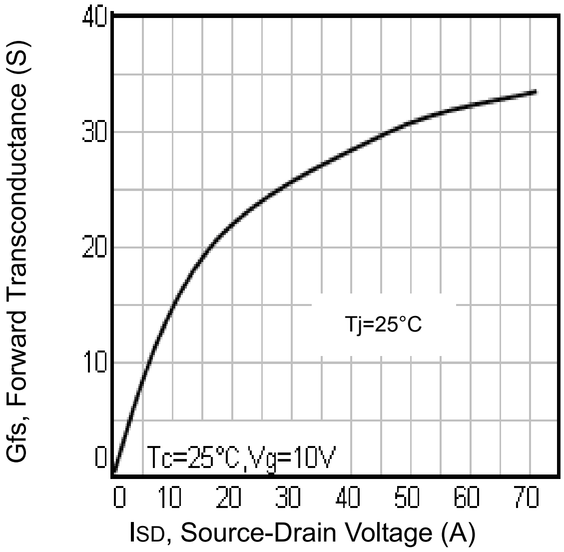


Fig5.Typical Forward Transconductance Vs. Drain Current

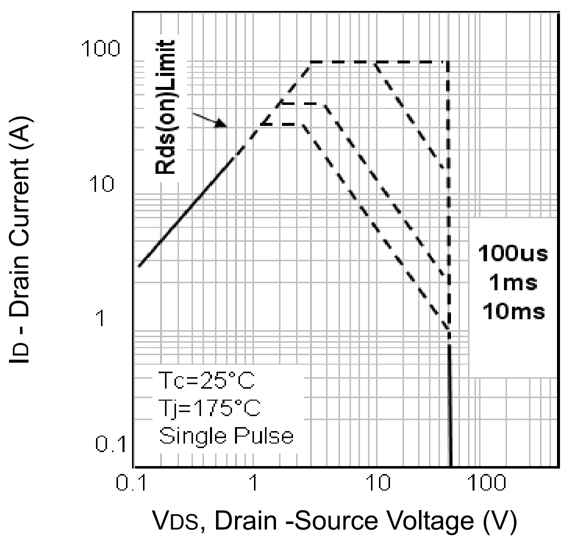


Fig6. Maximum Safe Operating Area

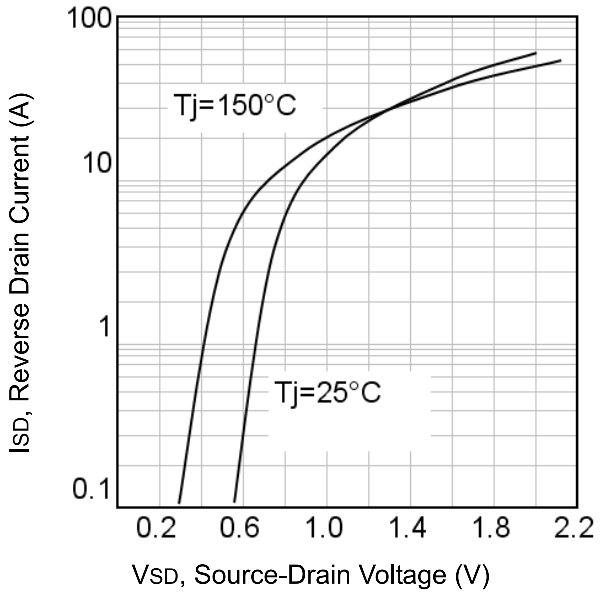


Fig7. Typical Source-Drain Diode Forward Voltage

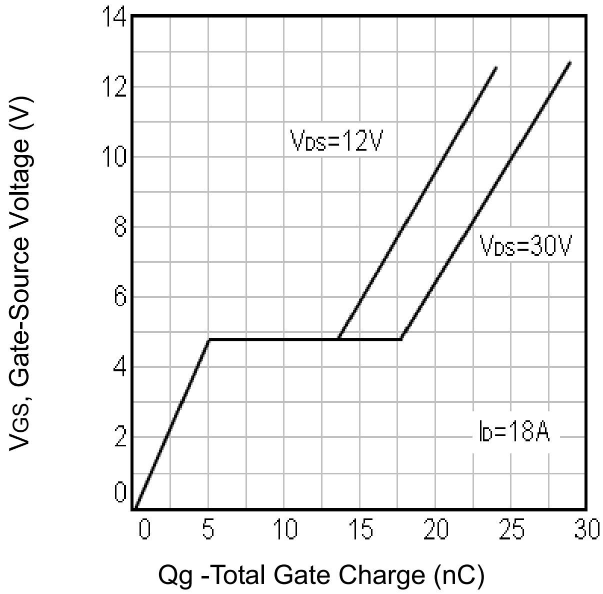


Fig8. Typical Gate Charge Vs.Gate-Source Voltage

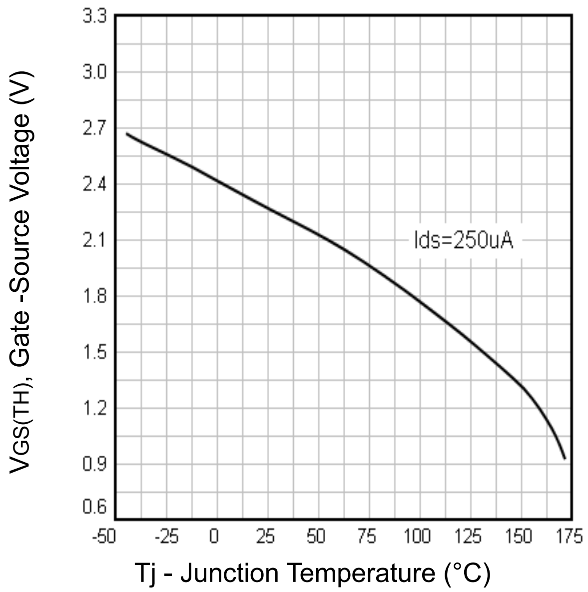


Fig9. Threshold Voltage Vs. Temperature

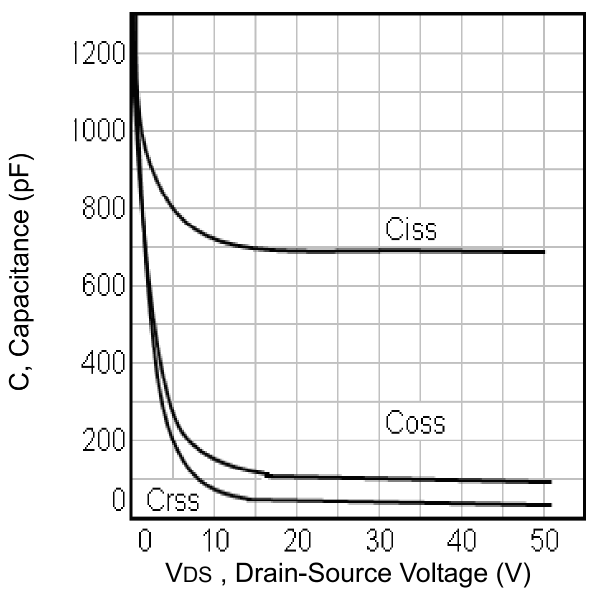


Fig10. Typical Capacitance Vs.Drain-Source Voltage

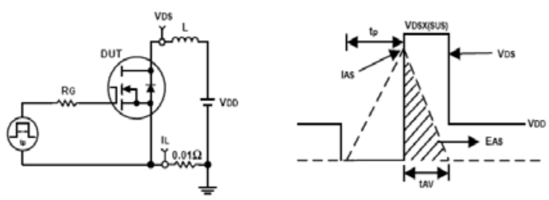


Fig11. Unclamped Inductive Test Circuit and waveforms

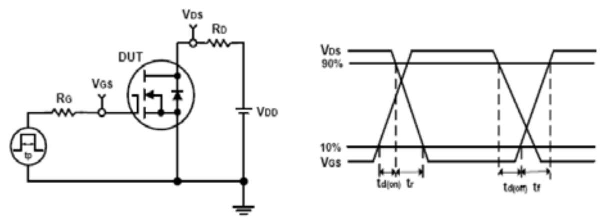


Fig12. Switching Time Test Circuit and waveforms

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